

3mm Silicon PD Chip datasheet

P/N : WS97-01C

Feature

Si PIN photodiode chip

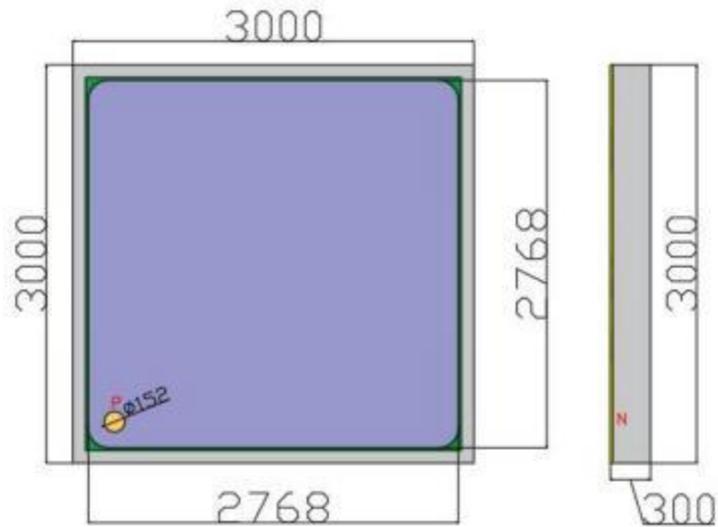
Structure

Planar type : PIN diode

Electrodes :

Back side (Cathode) : Au

Top side (Anode) : Al



DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	2768±20 x 2768±20			μm
Chip width	3000			μm
Chip length	3000			μm
Chip height	280	300	320	μm
Pad Area		152		μm

Electro-Optical Characteristics (@ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.5		1.3	V
Reverse Voltage	Vbr	Ir=100μA, H=0	35			V
Reverse Dark Current	Id	Vr=10V			10	nA
Sensitive Wavelength Range	λ		400	940	1100	nm
Capacitance	Cj	VR=3V, f=1MHz		23		pF